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PATENT APPLICATION
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10/13/00

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re patent application of: Sung Sik Jang

For: SEMICONDUCTOR PACKAGE HAVING IMPROVED ADHESIVENESS AND GROUND BONDING

BOX PATENT APPLICATION
Assistant Commissioner of Patents
Washington, D.C. 20231

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PATENT APPLICATION TRANSMITTAL LETTER

Transmitted herewith for filing, please find the following:

1. (XX) The specification of the above-referenced patent application is enclosed herewith (16 page(s) including claim(s) and Abstract).
2. (XX) 6 sheet(s) of:
X informal drawing(s) is (are) enclosed herewith.
_____ formal drawing(s) is (are) enclosed herewith.

3. (X) The fees for this application have been calculated and included as shown below (Prior to calculating the fees, please enter any enclosed preliminary amendment.):

	NO. FILED	NO. EXTRA	RATE	FEE
BASIC FEE				\$710
TOTAL CLAIMS	20-20	0	\$18	0
INDEPENDENT CLAIMS	3-3	0	\$80	0
MULTIPLE DEPENDENT CLAIM(S) PRESENTED			\$270	
TOTAL FEES:				\$710.00
Deduct One-Half for Small Entity Status				
Assignment Recordal Fee			\$40	
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5. (X) An oath or declaration is enclosed herewith that is:

X — Unsigned

— Newly executed per 37 CFR 1.63(a) and (b).

— A copy of the executed declaration filed in the prior application upon which priority is based, showing the signature or an indication thereon that it was signed; and:

— This application is being filed fewer than all of the inventors named in the prior application and it is requested that the following name or names be deleted from the list of inventors in the prior application for this continuation or divisional application:

— The prior application was accorded status under 37 CFR § 1.47 and is accompanied by:

— A copy of the decision granting a petition to accord Sec. 1.47 status to the prior application

(unless all of the inventors have or legal representatives have filed an oath or declaration to join in the prior application).

— A copy of the subsequently executed oath(s) or declaration(s) filed by the inventor(s) or legal representative(s) that have subsequently joined in the prior application.

6. (X) The power of attorney for this application:
— is appointed in the newly executed Oath or Declaration submitted herewith.
X is appointed by the power of attorney enclosed herewith.
— remains the same as originally in the parent application.
— was changed during the prosecution of the parent application and a copy of the change in the power of attorney is enclosed herewith.

7. (XX) The correspondence address for this application shall be:
Stanley R. Moore, Esq.
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3200 Fountain Place
1445 Ross Ave.
Dallas, Texas 75202
X which is a new correspondence address or a change therein.
— which is the same as originally in the parent application.
— which is the change in the correspondence address that was filed during the prosecution of the parent application.

8. (XX) Priority is hereby claimed under 35 USC 119 and 172 to the following foreign applications:

Country	Serial No.	Date
Korea	99-44653	Oct. 15, 1999

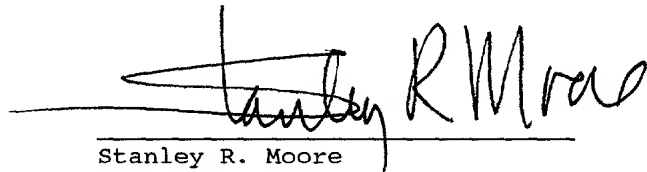
and:

— A certified copy of each application is enclosed herewith.
— A certified copy of each application was filed in prior application Serial No. _____.

9. () A verified statement claiming small entity status under 37 CFR 1.9 and 1.27:
— is enclosed herewith.
— was filed in parent application Serial No. _____, and such status remains unchanged and is requested for this application.
10. () A preliminary amendment is enclosed herewith.
11. () An Information Disclosure Statement with Modified PTO Form 1449 and a copy of the cited references are enclosed herewith.

12. () An Assignment of the invention to _____ with cover sheet and recordation fee is enclosed herewith for recordation by the Assignment Branch.
13. () The Commissioner is hereby authorized to charge payment, or to credit any overpayment, of the following fees associated with this filing or during the pendency of this application to Deposit Account No. _____.
- _____ Any patent application filing fees under 37 CFR 1.16.
 - _____ Any patent application processing fees under 37 CFR 1.17.
 - _____ The issue fee under 37 CFR 1.18 at or before mailing of the Notice of Allowance, pursuant to 37 CFR 1.311(b).
14. () Other (specify): _____
15. (XX) Confirmation Postcard.

Respectfully submitted,


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SEMICONDUCTOR PACKAGE HAVING IMPROVED
ADHESIVENESS AND GROUND BONDING5 TECHNICAL FIELD

The present invention relates in general to a semiconductor package, and more particularly but not by way of limitation, to a semiconductor package in which the adhesiveness between a chip paddle and a package body is improved, and the chip paddle ground-bonding is improved.

10 HISTORY OF RELATED ART

It is conventional in the electronic industry to encapsulate one or more semiconductor devices, such as integrated circuit dies, or chips, in a semiconductor package. These plastic packages protect a chip from environmental hazards, and provide a method of and apparatus for electrically and mechanically attaching the chip to an intended device. Recently, such semiconductor packages have included metal leadframes for supporting an integrated circuit chip which is bonded to a chip paddle region formed centrally therein. Bond wires which electrically connect pads on the integrated circuit chip to individual leads of the leadframe are then incorporated. A hard plastic encapsulating material, or encapsulant, which covers the bond wire, the integrated circuit chip and other components, forms the exterior of the package. A primary focus in this design is to provide the chip with adequate protection from the external environment in a reliable and effective manner.

As set forth above, the semiconductor package therein described incorporates a leadframe as the central supporting structure of such a package. A portion of the leadframe completely surrounded by the plastic encapsulant is internal to the package. Portions of the leadframe extend internally from the package and are then used to connect the package externally. More information relative to leadframe technology may be found in Chapter 8 of the book Micro Electronics Packaging Handbook, (1989), edited by R. Tummala and E. Rymaszewski and incorporated by reference herein. This book is published by Van Nostrand Reinhold, 115 Fifth Avenue, New York, New York.

Once the integrated circuit chips have been produced and encapsulated in semiconductor packages described above, they may be used in a wide variety of

5 electronic appliances. The variety of electronic devices utilizing semiconductor packages
has grown dramatically in recent years. These devices include cellular phones, portable
computers, etc. Each of these devices typically include a motherboard on which a
significant number of such semiconductor packages are secured to provide multiple
10 electronic functions. These electronic appliances are typically manufactured in reduced
sizes and at reduced costs, consumer demand increases. Accordingly, not only are
semiconductor chips highly integrated, but also semiconductor packages are highly
miniaturized with an increased level of package mounting density.

15 According to such miniaturization tendencies, semiconductor packages, which
transmit electrical signals from semiconductor chips to motherboards and support the
semiconductor chips on the motherboards, have been designed to have a small size. By
way of example only, such semiconductor packages may have a size on the order of
1x1mm to 10x10 mm. Examples of such semiconductor packages are referred to as MLF
(micro leadframe) type semiconductor packages and MLP (micro leadframe package)
20 type semiconductor packages. Both MLF type semiconductor packages and MLP type
semiconductor packages are generally manufactured in the same manner.

25 However, this conventional semiconductor package is problematic in that a
thickness of the silver plated layer formed on the upper faces of the chip paddle and the
internal leads deteriorate the adhesiveness between the package body and the chip paddle
or the internal leads. That is, the silver-plated layer is very weakly bonded to the package
body of the encapsulation material (the chip paddle or the side of the internal lead, both of
which are made of copper, are strongly bonded to the package body), so that interfacial
exfoliation is easily caused at the boundary between the package body and the silver-
30 plated layer. Further, moisture can readily permeate the semiconductor package through
the exfoliated portion, which may cause the semiconductor package to crack.

Usually a semiconductor chip or a chip paddle is ground-bonded by conductive
wires to achieve grounding or eliminate electrical noise problems. In this conventional
semiconductor package, the semiconductor chip is similar in area to the chip paddle, so
that there are no sufficient areas for ground bonding.

5 SUMMARY OF THE INVENTION

10 In one embodiment of the present invention, there is provided a semiconductor chip having an upper surface and a bottom surface. A plurality of input bond pads and output bond pads on the upper surface of the semiconductor chip and along the circumference of the semiconductor chip are electrically connected to the semiconductor chip. A chip paddle is provided which has a top surface, a side surface and a bottom surface. The chip paddle is bonded to the bottom surface of the semiconductor chip by an adhesive. The chip paddle has corners, a circumference and a half-etched section at the lower edge of the chip paddle along the chip paddle circumference.

15 A leadframe is provided having a plurality of tie bars. Each of the tie bars has a side surface and a bottom surface. The plurality of tie bars are connected to the corners of the chip paddle. The plurality of the tie bars externally extend from the chip paddle and have a half-etched section. A plurality of dam bars are provided on the leadframe help limit flow of encapsulation material on the leadframe.

20 A plurality of internal leads connect to the leadframe. Each of the leads has a side surface and a bottom surface. The leads are radially formed at regular intervals along and spaced apart from the circumference to the chip paddle and extend towards the chip paddle. Each of the leads has a step shaped half-etched section facing the chip paddle.

25 A ground ring is provided having an upper surface and a lower surface, and positioned between the semiconductor chip and the plurality of internal leads. The ground ring may interchangeably be used as a ground or a power ring. The upper surface of the ground ring is substantial planar with the upper surface of the semiconductor chip and the upper surface of the plurality of internal leads. A plurality of conductive wires are electrically connected to the plurality of internal leads and the semiconductor chip, wherein the conductive wires have a loop height between the leads and the semiconductor chip. Because of the planarity of the grounding leads and semi-conductor chip, the loop height of the conductive wires is minimized, which allows smaller packaging.

30 Encapsulating material encapsulates the semiconductor chip, conductive wires, chip paddle, and the leads to form a package body. The flow of the encapsulation material is limited by the dam bars formed on the leadframe. After encapsulation, the chip paddle, leads, and tie bars are externally exposed at respective side and bottom surfaces. The chip paddle further has through-holes in the half-etched section of the chip

- 5 paddle for increasing the bonding strength of the encapsulation material in the package body. In addition, tabs in the half-etched section of the chip paddle may be provided for the same purpose.

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5 BRIEF DESCRIPTION OF THE DRAWINGS

A more complete understanding of the method and apparatus of the present invention may be obtained by reference to the following detailed description when taken in conjunction with the accompanying Drawings wherein:

10 FIGURE 1 is a top plan view of the semiconductor chip of the present invention;
FIGURE 2 is a side elevation cross-section view of the semiconductor chip of
FIGURE 1 taken along line 2-2;
FIGURE 3 is a side elevation cross-section view of the semiconductor chip of
FIGURE 1 taken along line 3-3;
15 FIGURE 4 is a top plan view of a leadframe for the semiconductor package of the
present invention;
FIGURE 5 is a top plan view of an alternate embodiment for the semiconductor
package of the present invention; and
FIGURE 6 is a side elevation cross-section view of the semiconductor package of
20 FIGURE 5 taken along line 6-6.

DETAILED DESCRIPTION

Referring first to FIGS. 1 through 3, a semiconductor package 10 is shown
construed in accordance with the principals of the present invention. A semiconductor
25 package 10 includes a semiconductor chip 20 having an upper surface 30, a
circumference 40 and a bottom surface 50. A plurality of input bond pads 60 and output
bond pads 70 are disposed on the upper surface 30 of the semiconductor chip 20. A chip
paddle 80 having a top surface 90, a side surface 100 and a bottom surface 110 is secured
to the bottom surface 50 of the semiconductor chip 20 via an adhesive 120. The chip
30 paddle 80 has corners 130, a circumference 140 and a half-etched section 150. The half-
etched section 150 is located at a lower edge 160 of the chip paddle 80.

Referring now to FIGS. 1 through 4 in combination, a leadframe 170 is shown
having a plurality of tie bars 180, a side surface 190 and a bottom surface 200. The tie
bars 180 are connected to the corners 130 of the chip paddle 80. The tie bars 180
35 externally extend from the chip paddle 80. The leadframe 170 further has a half-etched
section 210 and a plurality of dam bars 220.

5 A plurality of leads 230 are connected to the leadframe 170 and have an upper surface 235 and a bottom surface 250. The leads 230 are radially formed at regular intervals along the circumference 140 and spaced apart from the circumference 140 of the chip paddle 80. The leads 230 extend towards the chip paddle 80, such that each of the plurality of leads 230 has a half-etched section 260 facing the chip paddle 80. It is to be
10 noted that the hatched areas in FIG. 1 are the half-etched sections of the paddle 80 and leads 230.

Referring to FIG. 2, there is disclosed a ground ring 262 formed in the half-etched section 150 of the chip paddle 80. The ground ring 262 is positioned between the semiconductor chip 20 and the plurality of leads 230. The ground ring may be
15 interchangeably used as a power ring should circumstances require. The upper surface 264 of the ground ring 262 is planar with the upper surface of the semiconductor chip 20 and the upper surface 235 of the leads 230.

A plurality of conductor wires 270 are provided and electrically connected to the plurality of leads 230 and the semiconductor chip 20. The plurality of conductive wires
20 270 have a loop height 275 between the plurality of leads 230 and the semiconductor chip 20. The loop height 275 of the conductive wires 270 is minimized from the upper surface 235 of the leads 230 and the upper surface 30 of the semiconductor chip 20. To form the semiconductor package 10, encapsulation material 280 encapsulates the semiconductor chip 20, conductive wires 270, chip paddle 80, and leads 230. Encapsulation material 280
25 may be thermoplastics or thermoset resins, with thermoset resins including silicones, phenolics, and epoxies. The dam bars 220 limit the flow of the encapsulation material 280 on the leadframe 170. During encapsulation, the chip paddle 80, leads 230, and tie bars 180 are externally exposed at the respective side and bottom surfaces. The side and/or bottom surfaces of chip paddle 80, leads 230, and tie bars 180 may be, but do not
30 necessarily have to be, electroplated with corrosion-minimizing materials such as tin lead, tin, gold, nickel palladium, tin bismuth, or similar alloys. In a first embodiment, the chip paddle 80 is provided with a plurality of through holes 300 in the half-etched section 150 for increasing the bonding strength of the encapsulation material 280 with the package 10.

The through holes 300 may be formed by chemical etching, such as when
35 patterning the entire leadframe 170 for forming the half-etched section 150 of the chip paddle 80. Alternatively, the through holes 300 may be formed by the use of a

5 mechanical punch or similar device. It should be noted that other methods may be used to form the through holes 300, and the present invention is not limited by the formation techniques disclosed herein.

10 Referring now to FIGS. 4 and 5 in combination, an alternate embodiment for the semiconductor package 10 is shown. In this embodiment, the chip paddle 80 is provided with a plurality of tabs 310 in the half-etched section 150 of the chip paddle 80 for the similar purpose of increased bonding strength. It is also contemplated that the combination of through holes 300 and tabs 310 may be used to increase the bonding strength of the encapsulation material 280 in the package 10.

15 The tabs 310 are formed in the half-etched section 150 of the chip paddle 80. The tabs 310 must extended to a limited degree to prevent a short circuit forming between the tabs 310 and the leads 230. It is preferable that the number of the tabs 310 corresponds to the number of the grounding input bond pads 60 and output bond pads 70 of the semiconductor chip 20. The tabs 310 may be formed by chemical etching when patterning the entire leadframe 170 and also by other mechanical methods depending on the requirements of the individual package 10. By increasing the area or length of the chip paddle 80, the tabs 310 are easily bonded with conductive wires 270 by increasing the area for which to connect the conductive wires 270. The tabs 310 may serve to function as a ground or power ring 262 in certain applications. It is to be noted that the hatched areas in FIG. 5 are the half-etched sections of the paddle 80 and leads 230.

25 As described previously, the use of the through holes 300 and tabs 310 increase the bonding strength to the encapsulation material 280, in addition to improving the fluidity of the encapsulation material 280 upon encapsulating. The presence of the through holes 300 and tabs 310 improves the fluidity of encapsulation material 280 by directing flow over or through the tabs 310 and through holes 300 in the package 10. In certain embodiments, as shown in FIGS. 2 and 3, a plated layer 320 of a material such as gold or silver may be applied to the upper surfaces 90, 235 of the chip paddle 80 and leads 230, respectively, to increase bonding strength to the wires 270.

30 It is thus believed that the operation and construction of the present invention will be apparent from the foregoing description of the preferred exemplary embodiments. While the semiconductor package having improved adhesiveness and crown bonding shown as described as being preferred, it will be obvious to a person of ordinary skill in

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Attorney Docket No.	Title of Application	First Named Inventor
45475-00015	Semiconductor Package Having Increased Solder Joint Strength	Kil Chin Lee
45475-00016	Clamp and Heat Block Assembly for Wire Bonding a Semiconductor Package Assembly	Young Suk Chung
45475-00018	Near Chip Size Semiconductor Package	Sean Timothy Crowley
45475-00019	Semiconductor Package	Sean Timothy Crowley
45475-00020	Stackable Semiconductor Package and Method for Manufacturing Same	Sean Timothy Crowley
45475-00021	Stackable Semiconductor Package and Method for Manufacturing Same	Jun Young Yang
45475-00024	Method of and Apparatus for Manufacturing Semiconductor Packages	Hyung Ju Lee
45475-00029	Semiconductor Package Leadframe Assembly and Method of Manufacture	Young Suk Chung

It is thus believed that the operation and construction of the present invention will be apparent from the foregoing description of the preferred exemplary embodiments. It will be obvious to a person of ordinary skill in the art that various changes and modifications may be made herein without departing from the spirit and the scope of the invention.

5 What is claimed is:

1. A packaged semiconductor, comprising:

a semiconductor chip having an upper surface, a circumference and a bottom surface;

10 a plurality of input bond pads and output bond pads on said upper surface along said circumference electrically connected to said semiconductor chip;

a leadframe having a chip paddle, said chip paddle having a top surface, a half-etched section, and a bottom surface, said chip paddle being bonded to said semiconductor chip by an adhesive, said leadframe having a plurality of tie bars, said plurality of tie bars each having a side surface and a bottom surface, each of said plurality of tie bars being connected to said corners of said chip paddle, said plurality of tie bars externally extending from said chip paddle, said leadframe having a plurality of dam bars;

a plurality of leads connected to said leadframe;

20 a plurality of wires electrically connected to said plurality of leads and said semiconductor chip; and

encapsulation material encapsulating said semiconductor chip, said plurality of conductive wires, said chip paddle, and said plurality of internal leads to form a package body;

25 wherein said chip paddle has a plurality of through-holes in said half-etched section of said chip paddle for increasing the bonding strength of said encapsulation material in said package body.

2. The packaged semiconductor of claim 1, wherein said chip paddle has a circumference and said half-etched section is located at a lower edge of said chip paddle along said chip paddle circumference.

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3. The packaged semiconductor of claim 1, wherein said plurality of tie bars each has a side surface and a bottom surface.

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4. The packaged semiconductor of claim 1 each of said plurality of tie bars externally extend has a half-etched section.

5. The packaged semiconductor of claim 1, further comprising a ground ring, said ground ring being electrically connected to said semiconductor chip by said conductive wires.

6. The packaged semiconductor of claim 1, wherein flow of said encapsulation material is limited by said plurality of dam bars formed on said leadframe.

7. The packaged semiconductor of claim 1, wherein said chip paddle has a plurality of tabs in said half-etched section of said chip paddle for increasing the bonding strength of said encapsulation material in said package body.

8. A packaged semiconductor, comprising:

a semiconductor chip having an upper surface, a circumference and a bottom surface;

a plurality of input bond pads and output bond pads on said upper surface along said circumference electrically connected to said semiconductor chip;

a leadframe having a chip paddle, said chip paddle having a top surface, a half-etched section, and a bottom surface, said chip paddle being bonded to said semiconductor chip

5 by an adhesive, said leadframe having a plurality of tie bars, said plurality of tie bars each having a side surface and a bottom surface, each of said plurality of tie bars being connected to said corners of said chip paddle, said plurality of tie bars externally extending from said chip paddle, said leadframe having a plurality of dam bars;

a plurality of leads connected to said leadframe;

10 a plurality of wires electrically connected to said plurality of leads and said semiconductor chip; and

encapsulation material encapsulating said semiconductor chip, said plurality of conductive wires, said chip paddle, and said plurality of internal leads to form a package body;

wherein said chip paddle has a plurality of tabs in said half-etched section of said chip paddle for increasing the bonding strength of said encapsulation material in said package body.

9. The packaged semiconductor of claim 8, wherein said chip paddle has a circumference and said half-etched section is located at a lower edge of said chip paddle along said chip paddle circumference.

10. The packaged semiconductor of claim 8, wherein said plurality of tie bars each has a side surface and a bottom surface.

25 11. The packaged semiconductor of claim 8 each of said plurality of tie bars externally extend has a half-etched section.

5 12. The packaged semiconductor of claim 8, further comprising a ground ring, said ground ring

being electrically connected to said semiconductor chip by said conductive wires.

10 13. The packaged semiconductor of claim 8, wherein flow of said encapsulation material is limited by said plurality of dam bars formed on said leadframe.

14. The packaged semiconductor of claim 8, wherein said chip paddle has a plurality of through-holes in said half-etched section of said chip paddle for increasing the bonding strength of said encapsulation material in said package body.

15. A packaged semiconductor, comprising:

a semiconductor chip having an upper surface, a circumference and a bottom surface;

a plurality of input bond pads and output bond pads on said upper surface along said circumference electrically connected to said semiconductor chip;

20 a leadframe having a chip paddle, said chip paddle having a top surface, a half-etched section, and a bottom surface, said chip paddle being bonded to said semiconductor chip by an adhesive, said leadframe having a plurality of tie bars, said plurality of tie bars each having a side surface and a bottom surface, each of said plurality of tie bars being connected to said corners of said chip paddle, said plurality of tie bars externally extending from said chip paddle, said leadframe having a plurality of dam bars;

25 a plurality of leads connected to said leadframe;

a plurality of wires electrically connected to said plurality of leads and said semiconductor chip; and

5 encapsulation material encapsulating said semiconductor chip, said plurality of
conductive wires, said chip paddle, and said plurality of internal leads to form a package body;

wherein said chip paddle has a plurality of through-holes in said half-etched section of
said chip paddle for increasing the bonding strength of said encapsulation material in said
package body; and

10 wherein said chip paddle has a plurality of through-holes in said half-etched section of
said chip paddle for increasing the bonding strength of said encapsulation material in said
package body.

15 16. The packaged semiconductor of claim 15, wherein said chip paddle has a circumference
and said half-etched section is located at a lower edge of said chip paddle along said chip
paddle circumference.

20 17. The packaged semiconductor of claim 15, wherein said plurality of tie bars each has a
side surface and a bottom surface.

18. The packaged semiconductor of claim 15 each of said plurality of tie bars externally
extend has a half-etched section.

25 19. The packaged semiconductor of claim 15, further comprising a ground ring, said ground
ring

being electrically connected to said semiconductor chip by said conductive wires.

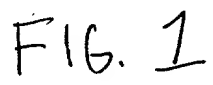
- 5 20. The packaged semiconductor of claim 15, wherein flow of said encapsulation material is limited by said plurality of dam bars formed on said leadframe.

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ABSTRACT OF THE INVENTION

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FIG. 2

A cross-sectional view of a semiconductor device 10. The device includes a substrate 110 with a central channel 80. A gate stack 20 is formed on the channel 80, consisting of a gate dielectric 270 and a gate electrode 280. Source/drain regions 120 are located on either side of the gate stack 20. A first insulating layer 100 is formed on the substrate 110, and a second insulating layer 150 is formed on the source/drain regions 120. A third insulating layer 230 is formed on the top surface of the device. A fourth insulating layer 235 is formed on the side surfaces of the device. A fifth insulating layer 250 is formed on the bottom surface of the device. A sixth insulating layer 260 is formed on the top surface of the device. A seventh insulating layer 270 is formed on the side surfaces of the device. An eighth insulating layer 280 is formed on the top surface of the device. A ninth insulating layer 30 is formed on the side surfaces of the device. A tenth insulating layer 320 is formed on the top surface of the device. A eleventh insulating layer 60 is formed on the side surfaces of the device. A twelfth insulating layer 70 is formed on the top surface of the device. A thirteenth insulating layer 140 is formed on the side surfaces of the device. A fourteenth insulating layer 150 is formed on the bottom surface of the device. A fifteenth insulating layer 160 is formed on the top surface of the device. A sixteenth insulating layer 170 is formed on the side surfaces of the device. A seventeenth insulating layer 180 is formed on the top surface of the device. An eighteenth insulating layer 190 is formed on the side surfaces of the device. A nineteenth insulating layer 200 is formed on the top surface of the device. A twentieth insulating layer 210 is formed on the side surfaces of the device. A twenty-first insulating layer 220 is formed on the top surface of the device. A twenty-second insulating layer 230 is formed on the side surfaces of the device. A twenty-third insulating layer 240 is formed on the top surface of the device. A twenty-fourth insulating layer 250 is formed on the side surfaces of the device. A twenty-fifth insulating layer 260 is formed on the top surface of the device. A twenty-sixth insulating layer 270 is formed on the side surfaces of the device. A twenty-seventh insulating layer 280 is formed on the top surface of the device. A twenty-eighth insulating layer 290 is formed on the side surfaces of the device. A twenty-ninth insulating layer 300 is formed on the top surface of the device. A thirtieth insulating layer 310 is formed on the side surfaces of the device. A thirty-first insulating layer 320 is formed on the top surface of the device. A thirty-second insulating layer 330 is formed on the side surfaces of the device. A thirty-third insulating layer 340 is formed on the top surface of the device. A thirty-fourth insulating layer 350 is formed on the side surfaces of the device. A thirty-fifth insulating layer 360 is formed on the top surface of the device. A thirty-sixth insulating layer 370 is formed on the side surfaces of the device. A thirty-seventh insulating layer 380 is formed on the top surface of the device. A thirty-eighth insulating layer 390 is formed on the side surfaces of the device. A thirty-ninth insulating layer 400 is formed on the top surface of the device. A fortieth insulating layer 410 is formed on the side surfaces of the device. A forty-first insulating layer 420 is formed on the top surface of the device. A forty-second insulating layer 430 is formed on the side surfaces of the device. A forty-third insulating layer 440 is formed on the top surface of the device. A forty-fourth insulating layer 450 is formed on the side surfaces of the device. A forty-fifth insulating layer 460 is formed on the top surface of the device. A forty-sixth insulating layer 470 is formed on the side surfaces of the device. A forty-seventh insulating layer 480 is formed on the top surface of the device. A forty-eighth insulating layer 490 is formed on the side surfaces of the device. A forty-ninth insulating layer 500 is formed on the top surface of the device. A fiftieth insulating layer 510 is formed on the side surfaces of the device. A fifty-first insulating layer 520 is formed on the top surface of the device. A fifty-second insulating layer 530 is formed on the side surfaces of the device. A fifty-third insulating layer 540 is formed on the top surface of the device. A fifty-fourth insulating layer 550 is formed on the side surfaces of the device. A fifty-fifth insulating layer 560 is formed on the top surface of the device. A fifty-sixth insulating layer 570 is formed on the side surfaces of the device. A fifty-seventh insulating layer 580 is formed on the top surface of the device. A fifty-eighth insulating layer 590 is formed on the side surfaces of the device. A fifty-ninth insulating layer 600 is formed on the top surface of the device. A sixtieth insulating layer 610 is formed on the side surfaces of the device. A sixty-first insulating layer 620 is formed on the top surface of the device. A sixty-second insulating layer 630 is formed on the side surfaces of the device. A sixty-third insulating layer 640 is formed on the top surface of the device. A sixty-fourth insulating layer 650 is formed on the side surfaces of the device. A sixty-fifth insulating layer 660 is formed on the top surface of the device. A sixty-sixth insulating layer 670 is formed on the side surfaces of the device. A sixty-seventh insulating layer 680 is formed on the top surface of the device. A sixty-eighth insulating layer 690 is formed on the side surfaces of the device. A sixty-ninth insulating layer 700 is formed on the top surface of the device. A seventieth insulating layer 710 is formed on the side surfaces of the device. A seventy-first insulating layer 720 is formed on the top surface of the device. A seventy-second insulating layer 730 is formed on the side surfaces of the device. A seventy-third insulating layer 740 is formed on the top surface of the device. A seventy-fourth insulating layer 750 is formed on the side surfaces of the device. A seventy-fifth insulating layer 760 is formed on the top surface of the device. A seventy-sixth insulating layer 770 is formed on the side surfaces of the device. A seventy-seventh insulating layer 780 is formed on the top surface of the device. A seventy-eighth insulating layer 790 is formed on the side surfaces of the device. A seventy-ninth insulating layer 800 is formed on the top surface of the device. An eightieth insulating layer 810 is formed on the side surfaces of the device. An eighty-first insulating layer 820 is formed on the top surface of the device. An eighty-second insulating layer 830 is formed on the side surfaces of the device. An eighty-third insulating layer 840 is formed on the top surface of the device. An eighty-fourth insulating layer 850 is formed on the side surfaces of the device. An eighty-fifth insulating layer 860 is formed on the top surface of the device. An eighty-sixth insulating layer 870 is formed on the side surfaces of the device. An eighty-seventh insulating layer 880 is formed on the top surface of the device. An eighty-eighth insulating layer 890 is formed on the side surfaces of the device. An eighty-ninth insulating layer 900 is formed on the top surface of the device. A ninetieth insulating layer 910 is formed on the side surfaces of the device. A ninety-first insulating layer 920 is formed on the top surface of the device. A ninety-second insulating layer 930 is formed on the side surfaces of the device. A ninety-third insulating layer 940 is formed on the top surface of the device. A ninety-fourth insulating layer 950 is formed on the side surfaces of the device. A ninety-fifth insulating layer 960 is formed on the top surface of the device. A ninety-sixth insulating layer 970 is formed on the side surfaces of the device. A ninety-seventh insulating layer 980 is formed on the top surface of the device. A ninety-eighth insulating layer 990 is formed on the side surfaces of the device. A ninety-ninth insulating layer 1000 is formed on the top surface of the device. A one-thousandth insulating layer 1010 is formed on the side surfaces of the device.

FIG. 3

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00E10T*E648950

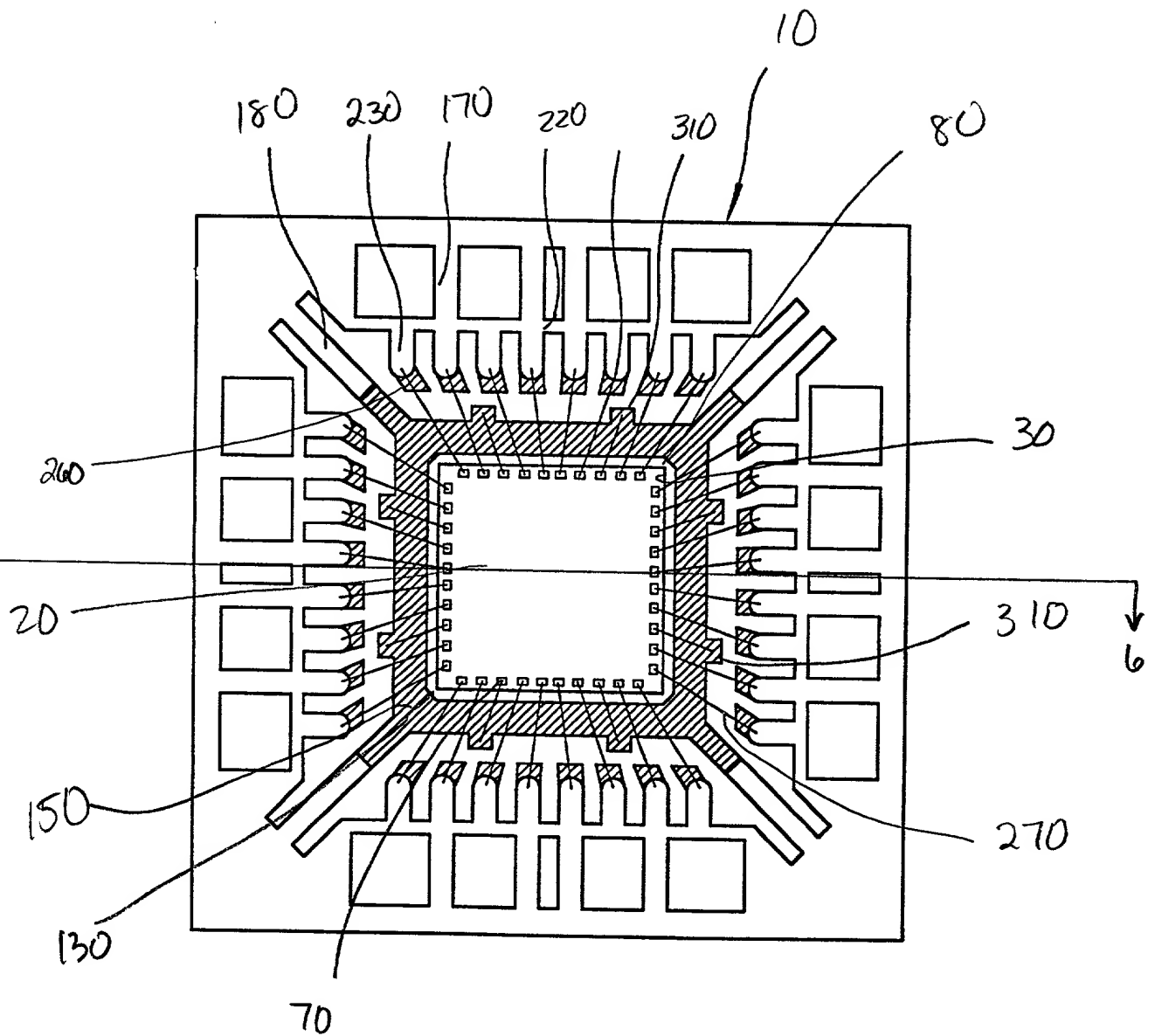


FIG. 5

A cross-sectional view of a semiconductor device 10. The device features a substrate 80 with a central channel 120. On the left and right sides of the channel, there are regions 110 and 150, respectively, which are part of a larger structure 230. Above the channel, there is a layer 20 containing a patterned region 30. This layer is flanked by regions 260 and 262. A layer 270 is positioned above the patterned region 30. The top surface of the device is indicated by a dashed line 280. A region 235 is shown on the right side of the device, and a region 70 is located within the patterned region 30. A region 60 is also indicated within the patterned region 30. A region 320 is shown on the left side of the device, and a region 264 is located within the patterned region 30.

FIG. 6

**RULES 63 AND 67 (37 C.F.R. 1.63 and 1.67)
DECLARATION AND POWER OF ATTORNEY**

FOR UTILITY/DESIGN/CIP/PCT NATIONAL APPLICATIONS

As a below named inventor, I hereby declare that:

My residence, post office address and citizenship are as stated below next to my name; and

I believe that I am the original, first and sole inventor (if only one name is listed below) or an original, first and joint inventor (if plural names are listed below) of the subject matter which is claimed and for which a patent is sought on the invention entitled: **SEMICONDUCTOR PACKAGE HAVING IMPROVED ADHESIVENESS AND GROUND BONDING**, the specification of which: (mark only one)

- X (a) is attached hereto.
— (b) was filed on _____ as Application Serial No. _____ and was amended on _____ (if applicable)
— (c) was filed as PCT International Application No. PCT/_____ on _____ and was amended on _____ (if applicable).
— (d) was filed on _____ as Application Serial No. _____ and was issued a Notice of Allowance on _____.
— (e) was filed on _____ and bearing attorney docket number _____

I hereby state that I have reviewed and understand the contents of the above identified specification, including the claims as amended by any amendment referred to above or as allowed as indicated above.

I acknowledge the duty to disclose all information known to me to be material to the patentability of this application as defined in 37 CFR § 1.56. If this is a continuation-in-part (CIP) application, insofar as the subject matter of each of the claims of this application is not disclosed in the prior United States application in the manner provided by the first paragraph of 35 U.S.C. § 112, I acknowledge the duty to disclose to the Office all information known to me to be material to patentability of the application as defined in 37 CFR § 1.56 which became available between the filing date of the prior application and the national or PCT international filing date of this application.

I hereby claim foreign priority benefits under 35 U.S.C. § 119/365 of any foreign application(s) for patent or inventor's certificate listed below and have also identified below any foreign application for patent or inventor's certificate filed by me or my assignee disclosing the subject matter claimed in this application and having a filing date (1) before that of the application

on which my priority is claimed or, (2) if no priority is claimed, before the filing date of this application:

PRIOR FOREIGN PATENTS

<u>Number</u>	<u>Country</u>	<u>Month/Day/Year Filed</u>	<u>Date first laid-open or Published</u>	<u>Date patented or Granted</u>	<u>Priority Claimed Yes No</u>
99-44653	Korea	Oct. 15, 1999			XX

I hereby claim the benefit under 35 U.S.C. § 120/365 of any United States application(s) listed below and PCT international applications listed above or below:

PRIOR U.S. OR PCT APPLICATIONS

<u>Application No. (series code/serial no.)</u>	<u>Month/Day/Year Filed</u>	<u>Status(pending, abandoned, patented)</u>
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NONE

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all of the firm of **JENKENS & GILCHRIST, a Professional Corporation**, 1445 Ross Avenue, Suite 3200, Dallas, Texas 75202-2799, as my attorneys and/or agents, with full power of substitution and revocation, to prosecute this application, provisionals thereof, continuations, continuations-in-part, divisionals, appeals, reissues, substitutions, and extensions thereof and to transact all business in the United States Patent and Trademark Office connected therewith, to appoint any individuals under an associate power of attorney and to file and prosecute any international patent application filed thereon before any international authorities, and I hereby authorize them to act and rely on instructions from and communicate directly with the person/assignee/attorney/firm/organization who/which first sent this case to them and by whom/which I hereby declare that I have consented after full disclosure to be represented unless/until I instruct them in writing to the contrary.

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I hereby declare that all statements made herein of my own knowledge are true and that all statements made on information and belief are believed to be true; and further that these statements were made with the knowledge that willful false statements and the like so made are punishable by fine or imprisonment, or both, under Section 1001 of Title 18 of the United States Code, and that such willful false statements may jeopardize the validity of the application or any patent issued thereon.

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